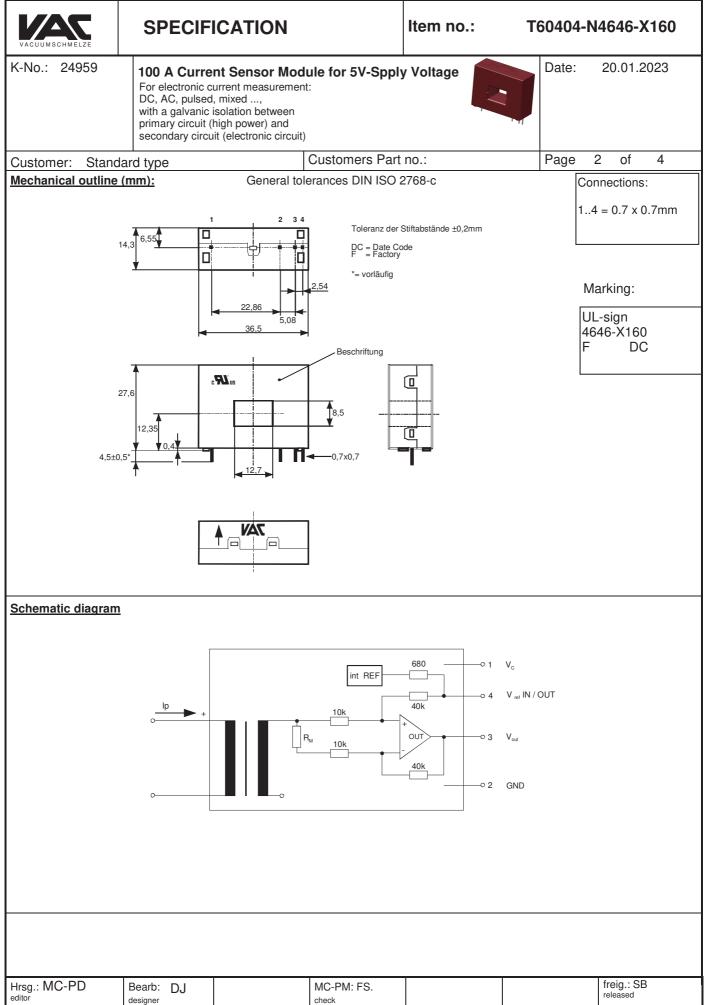
()) _ () _	SPECIFICATION	Item r	10.:	T60404-I	N4646-X160
K-No.: 24959	100 A Current Sensor Module for 5 For electronic current measurement: DC, AC, pulsed, mixed, with a galvanic isolation between primary circuit (high power) and secondary circuit (electronic circuit)	V-Spply Voltag	e	Date:	20.01.2023
Customer: Stan	dard type Custome	ers Part no.:		Page	1 of 4
Description Closed loop (comp Current Sensor with field probe Printed circuit boar Casing and materia	Characteristics ensation) Excellent accuracy n magnetic Very low offset current Very low temperature dependence current drift	A M a ency and offset	 AC varia drives Static co Battery s Switchec Power Si 	S	ation in industrial and servo motor notor drives ons ipplies (SMPS) ig applications
<u> Electrical data – R</u>	atings	min.	typ.	max.	Einheit
IPN	Primary nominal r.m.s. current		1(00	А
Vout	Output voltage @ I _P		V	Ref ± (0.625*IP/I	pn) V
Vout	Output voltage @ IP=0, TA=25°C		V	Ref ± 0.0025	V
V _{Ref}	Reference voltage external	0		4	V
V _{Ref}	Reference voltage internal		2.	5 ± 0.005	V
K _N	Turns ratio		1	: 1000	
	ie werfermenen dete				
<u>iccuracy – Dynan</u>	ic performance data	min.	typ.	max.	Unit
I _{P,max}	Max. measuring range	±230			
X	Accuracy @ I _{PN} , T _A = 25°C			1	%
εL	Linearity			0.1	%
Vout -2,5V	Offset voltage @ IP=0, TA= 25°C			±2.5	mV
	U - 1	0500	3	10	ppm/K
$\Delta V_{out}/2.5V/\Delta T$	Temperature drift of $V_{out} @ I_P=0$. $T_{A=} -40$.85°C			
$\Delta V_{out}/2,5V/\Delta T$	Temperature drift of V _{out} @ I _{P=0} , T _{A=} -40 Response time @ 80% von I _{PN}	.85°C	1		us
tr	Response time @ 80% von IPN	.85°U	1		μs µs
		.85°C DC10	1		μs μs kHz
tr ∆t (IP,max) f	Response time @ 80% von I _{PN} Delay time at di/dt = 100 A/μs		1		μs
tr ∆t (I _{P,max}) f General data	Response time @ 80% von I _{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth		1	max.	µs kHz Unit
tr ∆t (I _{P,max}) f General data T _A	Response time @ 80% von I _{PN} Delay time at di/dt = 100 A/μs	DC10	1 1 0	max. +85	µs kHz
tr ∆t (I _{P,max}) f seneral data	Response time @ 80% von I _{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth	DC10 <mark>min.</mark>	1 1 0 typ.		μs kHz Unit
tr <u>∆t (I_{P,max})</u> f teneral data T _A T _S m	 Response time @ 80% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass 	DC10 <mark>min.</mark> -40 -40	1 1 0 typ. 18	+85 +85	µs kHz <mark>Unit</mark> °C °C g
tr At (I _{P,max}) f teneral data T _A T _S m V _C	Response time @ 80% von I _{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage	DC10 <mark>min.</mark> -40	1 1 0 typ. 18 5	+85	μs kHz °C °C g V
tr Δt (I _{P,max}) f eneral data Ta Ts m V _C Ico	Response time @ 80% von I _{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption	DC10 min. -40 -40 4.75	1 1 0 typ. 18	+85 +85	μs kHz <mark>Unit</mark> °C °C g
tr <u>At (I_{P,max})</u> f <u>General data</u> <u>T</u> A Ts m Vc Ico S _{clear}	 Response time @ 80% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Clearance (component without solder pad) 	DC10 min. -40 -40 4.75 12	1 1 0 typ. 18 5	+85 +85	μs kHz °C °C g V mA mm
tr <u>At (IP,max)</u> f General data TA TS M VC Ico Sclear Screep	 Response time @ 80% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Clearance (component without solder pad) Creepage (component without solder pad) 	DC10 min. -40 -40 4.75	1 1 0 typ. 18 5	+85 +85 5.25	μs kHz °C °C g V mA mm mm
tr <u>∆t (IP,max)</u> f Seneral data TA Ts m Vc Ico Sclear Screep Vsys	 Response time @ 80% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Clearance (component without solder pad) Creepage (component without solder pad) System voltage overvoltage category III 	DC10 min. -40 -40 4.75 12 12	1 1 0 typ. 18 5	+85 +85	μs kHz °C °C g V mA mm
tr <u>∆t (IP,max)</u> f General data TA Ts m Vc Ico Sclear Screep	 Response time @ 80% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Clearance (component without solder pad) Creepage (component without solder pad) System voltage overvoltage category III Working voltage (table 3 acc. to IEC 611 	DC10 min. -40 -40 4.75 12 12	1 1 0 typ. 18 5	+85 +85 5.25 600	μs kHz °C °C g V mA mm mm V _{RMS}
tr <u>∆t (IP,max)</u> f General data TA Ts m Vc Ico Sclear Screep Vsys	 Response time @ 80% von I_{PN} Delay time at di/dt = 100 A/µs Frequency bandwidth Ambient operating temperature Ambient storage temperature Mass Supply voltage Current consumption Clearance (component without solder pad) Creepage (component without solder pad) System voltage overvoltage category III 	DC10 min. -40 -40 4.75 12 12	1 1 0 typ. 18 5	+85 +85 5.25	μs kHz °C °C g V mA mm mm



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K-No.: 24959 <u>Customer: Standa</u> <u>Electrical Data</u> VCtot	For electror DC, AC, pu with a galva primary circ secondary o	rrent Sensor Module f nic current measurement: lsed, mixed, nic isolation between uit (high power) and circuit (electronic circuit) Cus	for 5V-Spply Voltage tomers Part no.:		Date: 2 Page 3	20.01.2023 of 4
lectrical Data	rd type	Cus	tomers Part no.:		Page 3	of 4
V _{Ctot}			min.	typ.	max.	Unit
	Maximum s	upply voltage (without funct		.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	6	V
lc		rent with primary current		A +Ip*KN+Voi	ut/RL	mA
lout,SC		t output current		±20		mA
Rs	Secondary	coil resistance @ T _A =85°C)		14	Ω
R _{i,Ref}	-	istance of Reference input		670		Ω
Ri,(Vout)		stance of V _{out}			1	Ω
RL		commended resistance of	Vout 1			kΩ
CL		commended capacitance of			500	pF
ΔΧ _{Τi} /ΔΤ		re drift of X @ $T_A = -40 \dots -$			40	ppm/K
$\Delta V_0 = \Delta (V_{out} - V_{Ref})$		offset drift including:		2	6	mV
Vot	Long term of	0		1		mV
Vot	, e	re drift von V ₀ @ T _A = -40 .	+85°C	1		mV
V _{0H}		of Vout @ IP=0 (after an over			0.7	mV
$\Delta V_0 / \Delta V_C$	Supply volta	age rejection ratio			1	mV/V
Voss		(with 1 MHz- filter first or	der)		20	mV
Voss		(with 100 kHz- filter firdt o		2.5	6	mV
Voss	Offsetripple	(with 20 kHz- filter first or	der)	0.7	1.5	mV
C _k	Mechanical Settings: 10	ossible coupling capacity stress according to M320) Hz, 1 min/Oktave, 2 hour	9/3 's	6		pF
		perature balance of the samp	•	-	,	
V_{out} - V_{Ref} (IP=0) (V)	M3226:	Output voltage vs. interna Offset voltage	al reference (I _P =100A, 40)-80Hz)	625±0.7% ± 0.0025	mV V
V _d (V)	M3014:	Test voltage, RMS, 1 s pin 1-4 to inner hole			1.8	kV
Ve (AQI	L 1/S4):	Partial discharge voltage with V_{vor}	acc.M3024		1500 1875	Vrms Vrms
Type Testing (Pin 1-4	to inner hole)				
Vw	HV transier	nt test according to M3064	(1,2 µs / 50 µs-wave fo	orm)	8	kV
V _d		age to M3014		(5 s)	3.6	kV
Ve	Partial discl with Vvor	harge voltage acc.M3024			1500 1875	V _{RMS} V _{RMS}

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	HMELZE	SPECIFIC	ATION		Item no.:	160404-1	N4646-X160
K-No.: 2	24959	100 A Current For electronic curre DC, AC, pulsed, m with a galvanic isol primary circuit (high secondary circuit (high	ixed, ation between n power) and	for 5V-Spply	Voltage	Date:	20.01.2023
Custome	r: Stand	ard type	Cus	stomers Part	no.:	Page	4 of 4
		eral of the terms us	ed in the tablets (in alphabetica	l order)		
tr: ∆t (I _{Pmax}):	at I _P = 0. Delay tin	se time (describe the 8 \cdot I _{PN} between a re ne (describe the dyn ad between I _{Pmax} and	ctangular current a amic performance	nd the output v for the rapid cu	voltage V _{OUt} (I _p) urrent pulse rate e.	g short circuit cu	rrent)
	measure		the output voltage	vout(IPmax) vviti	r a primary current		00 Α/μS.
Upd	Rated disc UPD	charge voltage (recu = $\sqrt{2} * V_{work}$	rring peak voltage	separated by th	ne insulation) prov	ed with a sinusoi	dal voltage V _{work}
Vvor	test in IEC	bltage is the RMS va 61800-5-1:2007 = 1.875 *UPD / √2	lve of a sinusoidal	voltage with pe	eak value of 1.875	* U_{PD} required for	or partial dischar
	Vvor	= 1.8/5 UPD / N2					
Vsys	System vo	ltage value of ra	ted voltage accordi	ng to IEC 6180	0-5-1:2007.		
Vwork	Working v	oltage voltage acc	cording to IEC 618	00-5-1:2007			
	which occ	urs by design in a ci	cuit or across insu	lation.			
V ₀ :		oltage between V _{out} a (0) - 2.5V	and the rated refere	ence voltage of	$V_{\text{ref}} = 2.5 V.$		
V _{0H} :	Zero var	iation of V₀ after ove	rloading with a DC	of tenfold the r	ated value		
V _{0t} :	Long ter	m drift of V_{\circ} after 10	0 temperature cycl	es in the range	-40 bis 85 °C.		
X:	Permissi	ble measurement er	ror in the final insp	ection at RT. d	efined bv		
		$00 \cdot \left \frac{\mathrm{V}_{\mathrm{out}}(I_{PN}) - \mathbf{V}_{\mathrm{out}}(I_{PN})}{0,625 \mathrm{V}} \right $,.			
X _{ges} (I _{PN}):		ble measurement er $00 \cdot \left \frac{V_{out} (I_{PN}) - 2.5}{0.625 V} \right $				-	easurement I _{PN}
εL:	Linearity	fault defined by	$\varepsilon_{\rm L} = 100 \cdot \left \frac{\rm I_{\rm P}}{\rm I_{\rm PN}} - \right $	$-\frac{\mathrm{V}_{out}(I_{P})-V}{\mathrm{V}_{out}(I_{PN})-V}$	$\left \frac{V_{out}(0)}{V_{out}(0)} \right %$		
Hrsg.: MC	-PD	Bearb: DJ	M	C-PM: FS.			freig.: SB released

 editor
 designer
 check

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